# **S71NS-N MCP Products**

MirrorBit® 1.8 Volt-only Simultaneous Read/Write, Burst-mode Multiplexed Flash Memory 256 Mb (16 Mb x 16-bit), 128 Mb (8 Mb x 16-bit) and 64 Mb (4 Mb x 16-bit) with Multiplexed pSRAM 64 Mb (4 Mb x 16-bit), 32 Mb (2 Mb x 16-bit), 16 Mb (1 Mb x 16-bit) and 8Mb (512Kb x 16-bit)



Data Sheet (Advance Information)

**Notice to Readers:** This document states the current technical specifications regarding the Spansion product(s) described herein. Each product described herein may be designated as Advance Information, Preliminary, or Full Production. See *Notice On Data Sheet Designations* for definitions.



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# **S71NS-N MCP Products**

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256 Mb (16 Mb x 16-bit), 128 Mb (8 Mb x 16-bit) and 64 Mb (4 Mb x 16-bit) with Multiplexed pSRAM 64 Mb (4 Mb x 16-bit), 32 Mb (2 Mb x 16-bit), 16 Mb (1 Mb x 16-bit) and 8Mb (512Kb x 16-bit)

Data Sheet (Advance Information)



## **Features**

- Power supply voltage of 1.7 V to 1.95 V
- Burst Speed: 66 MHz

- Package MCP BGA: 0.5 mm ball pitch
  - 8.0 x 9.2 mm, 56 ball for other NS064N and NS128N based MCPs
  - 10.0 x 11.0 mm, 60 ball for NS256N based MCPs
- Operating Temperature
  - Wireless, -25°C to +85°C (Note 1)

## **General Description**

The S71NS-N Series is a product line of stacked Multi-Chip Product (MCP) packages and consists of the following items:

- One or more S29NS-N flash memory die
- Mux burst-mode pSRAM

The products covered by this document are listed in the table below. For details about their specifications, please refer to their individual datasheet for further details.

	pSRAM				
	Density	8 Mb	16 Mb	32 Mb	64 Mb
	64 Mb	S71NS064N80 (2)	S71NS064NA0	S71S064NB0	
Flash	128 Mb (2)		S71NS128NA0	S71NS128NB0	S71NS128NC0
	256 Mb (2)			S71NS256NB0	S71NS256NC0

#### Note

- 1. Absolute maximum storage temperature ratings for MCPs is identical to single chip ratings listed in stand-alone Flash data sheet.
- 2. Not recommended for new designs. Use S71VS064R, S71VS128R, and S71VS256R instead.

For detailed specifications, please refer to the individual data sheets:

Document	Publication Identification Number	
S29NS-N	S29NS-N_00	
8 Mb Multiplexed pSRAM Type 1	muxpSRAM_09	
16 Mb Multiplexed pSRAM Type 1	muxpSRAM_00	
16 Mb Multiplexed pSRAM Type 3	muxpsram_03	
32 Mb Multiplexed pSRAM Type 3	muxpsram_10	
64 Mb Multiplexed pSRAM Type 3	muxpsram_01	

Publication Number S71NS-N 00

Revision A

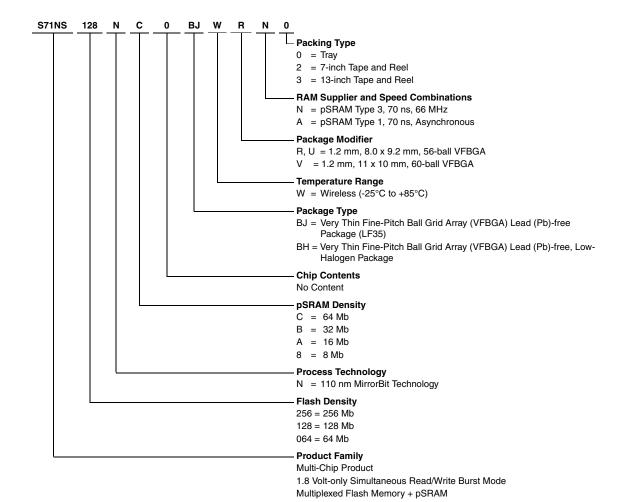
Amendment 9

Issue Date April 15, 2009



## 1. Ordering Information

The order number is formed by a valid combinations of the following:





## 1.1 Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult your local sales office to confirm availability of specific valid combinations and to check on newly released combinations.

Table 1.1 MCP Configurations and Valid Combinations

Base Ordering Part Number (1)	Package & Temperature	Model Number	Packing Type	pSRAM Type	Flash Speed Options	pSRAM Speed Options
S71NS064N80 (2)	BJW, BHW	RA		pSRAM Type 1	66 MHz	Asynchronous
C71NCOC4NAO				pSRAM Type 1	66 MHz	Asynchronous
S71NS064NA0		RN		pSRAM Type 3	66	MHz
S71NS064NB0	BJW, BHW	UN		pSRAM Type 3	66	MHz
S71NS128NA0 (2)	BJW	RN	0, 2, 3	pSRAM Type 3	66	MHz
S71NS128NB0 (2)		RN		pSRAM Type 3	66	MHz
S71NS128NC0 (2)		RN		pSRAM Type 3	66	MHz
S71NS256NB0 (2)		VN		pSRAM Type 3	66	MHz
S71NS256NC0 (2)		VN		pSRAM Type 3	66	MHz

### Note

- 1. The package marking omits the leading S from the ordering part number.
- $2. \ \ \textit{Products no longer recommended for new designs.} \ \ \textit{Please contact local Spansion sales representative for recommended migratory path.}$



# 2. Input/Output Descriptions

Table 2.1 identifies the input and output package connections provided on the device.

Table 2.1 Input/Output Descriptions

Symbol	Description		RAM
AMAX – A16	Address inputs	Х	Х
ADQ15 – ADQ0	Multiplexed Address/Data	Х	Х
OE#	Output Enable input. Asynchronous relative to CLK for the Burst mode.	Х	Х
WE#	Write Enable input.	Х	Х
V <sub>SS</sub>	Ground	Х	Х
NC	No Connect; not connected internally	Х	Х
RDY	Ready output. Indicates the status of the Burst read. The WAIT# pin of the pSRAM is tied to RDY.	Х	х
CLK	Clock input. In burst mode, after the initial word is output, subsequent active edges of CLK increment the internal address counter. Should be at V <sub>IL</sub> or V <sub>IH</sub> while in asynchronous mode	х	Х
AVD#	Address Valid input. Indicates to device that the valid address is present on the address inputs.  Low = for asynchronous mode, indicates valid address; for burst mode, causes starting address to be latched.  High = device ignores address inputs		х
F-RST#	Hardware reset input. Low = device resets and returns to reading array data		
F-WP#	Hardware write protect input. At $V_{IL}$ , disables program and erase functions in the four outermost sectors. Should be at $V_{IH}$ for all other conditions.		
F-ACC	Accelerated input. At $V_{HH}$ , accelerates programming; automatically places device in unlock bypass mode. At $V_{IL}$ , disables all program and erase functions. Should be at $V_{IH}$ for all other conditions.		
R-CE1#	Chip-enable input for pSRAM.		Х
F-CE#	Chip-enable input for Flash. Asynchronous relative to CLK for Burst Mode.	Х	
R-CRE	Control Register Enable (pSRAM).		Х
F-VCC	Flash 1.8 Volt-only single power supply.	Х	
R-VCC	pSRAM Power Supply.		Х
R-UB#	Upper Byte Control (pSRAM).		Х
R-LB#	Lower Byte Control (pSRAM)		Х
DNU	Do Not Use		



## 3. MCP Block Diagram

F-RST# RST# F-ACC ACC NS WP# RDY F-WP# RDY/ WAIT F-CE# CE# OE# OE# AD15-AD0 AD15-AD0 WF# WE# AVD# AVD# CLK CLK Amax-A16 Amax-A16 OE# WE# AVD# CLK WAIT pSRAM R-CE# CE# R-CRE CRE AD15-AD0 R-UB# UB# R-LB# LB# Amax-A16

Figure 3.1 MCP Block Diagram

The CLK and WAIT signals on the pSRAM are not present on the pSRAM Type 2; therefore, for those MCP's, those signals will only be connected to the NS flash, but not to the pSRAM. Also, on this pSRAM, the CRE signal will not be present at all.

# 4. Connection Diagrams/Physical Dimensions

This section contains the I/O designations and package specifications for the S71NS-N.

# 4.1 Special Handling Instructions for FBGA Packages

Special handling is required for Flash Memory products in FBGA packages.

Flash memory devices in FBGA packages may be damaged if exposed to ultrasonic cleaning methods. The package and/or data integrity may be compromised if the package body is exposed to temperatures above 150°C for prolonged periods of time.



## 4.2 Connection Diagrams

## 4.2.1 pSRAM Based Pinout, 56-Ball, VFBGA

56-ball Fine-Pitch Ball Grid Array (Top View, Balls Facing Down) No Connect (Distance betwee outer NC balls is 2x pitch) (C11) Reserved for Future Use RFU D4 D9 F-ACC (D11 D3 D5 D7 (D8) D6 (D10) Flash/RAM Shared Only F-RDY/ R-WAIT CLK  $V_{SS}$ V<sub>CC</sub> E4 E6 E11 E8 E9 E3 E5 E10 ( E7 ) A20 AVD# DNU Flash Only F3 F4 F5 F6 F7 F8 F9 F10 F11 F12 RAM Only A/DQ13 A/DQ12 Vss G3 G4 G5 G6 G7 G8 G9 G10 G11 (G12 A/DQ15 A/DQ14 A/DQ4 A/DQ11 A/DQ10 A/DQ1 A/DQ0 A/DQ5 H12 H3 NC (H4) (H11) (H7) (на) R-CRE R-CE#

Figure 4.1 pSRAM Based Pinout, 56-Ball, VFBGA

## Notes

- Addresses are shared between Flash and RAM depending on the density of the pSRAM.
- 2. CLK and WAIT signals are Flash only for the S71NS064NA0-RT, while on that MCP, the CRE signal won't exist.

MCP	Flash-Only Addresses	Shared Addresses	Shared ADQ Pins
S71NS128NC0	A22	A21-A16	
S71NS128NB0	A22-A21	A20-A16	
S71NS128NA0	A22-A20	A19-A16	ADQ15 – ADQ0
S71NS064NB0	A21	A20-A16	ADQ15 – ADQ0
S71NS064NA0	A21-A20	A19-A16	
S71NS064N80	A21-A19	A18-A16	



## 4.2.2 pSRAM Based Pinout, 60-Ball, VFBGA

(E13) F10 WE# F13 Flash/RAM Shared Only (G14) G12 A18 G5 G7 G10 F-RST# G11 F-WP# G6 (G8) G9 AVD# H5 (H6) Н7 (H12 (H14) Н8 ( H9 ) (н10) (H11) (H13) A/DQ13 A/DQ12 A/DQ3 A/DQ2 RAM Only ( J5 ) J6 ) J7 ) J8 J9 J10 (J11 J12 J13) (J14` A/DQ4 A/DQ11 A/DQ10 A/DQ1 A/DQ0 A/DQ5 (K10) ( K6 ) ( K9 ) (K13) P18 NC

Figure 4.2 pSRAM Based Pinout, 60-Ball, VFBGA

Note

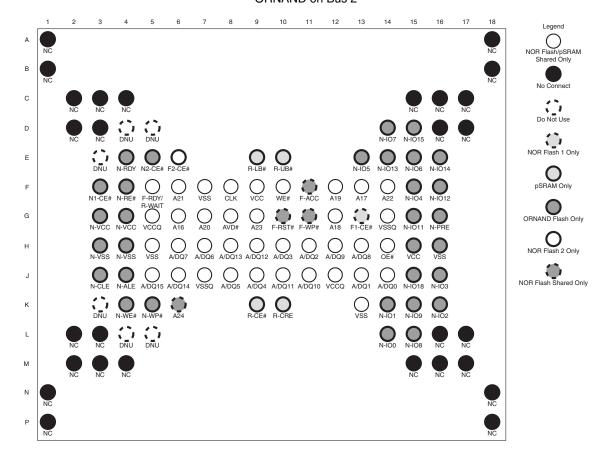
Addresses are shared between Flash and RAM depending on the density of the pSRAM.

MCP	MCP Flash-Only Addresses Shared Addresses		Shared ADQ Pins
S71NS256NC0	A23-A22	A21-A16	ADQ15–ADQ0
S71NS256NB0	A23-A21	A20-A16	ADQ15-ADQ0



## 4.2.3 Look Ahead Connection Diagram

Figure 4.3 112-ball x16 MUX NOR Flash + x16 MUX pSRAM on Shared Bus and x16 NAND Interface ORNAND on Bus 2

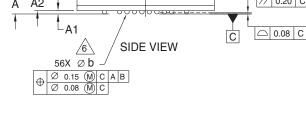




#### 4.3 **Physical Dimensions**

#### 4.3.1 NLB056—9.2 x 8.0 mm, 56-ball VFBGA

Figure 4.4 NLB056—56-ball VFBGA D1 A D еD ○ 0.10 C (2X) 14 13 12 11 10 ++000000+++0000++ SE 7 Е E1 еĒ F E D C B A KJHG INDEX MARK В PIN A1 <u>/</u>9\ CORNER **CORNER** SD TOP VIEW △ 0.10 C (2X) **BOTTOM VIEW** // 0.20 C A2 Α ĹA1 ○ 0.08 C С SIDE VIEW <u>/6\</u> 56X ∅ b



DAOKAOE		NII D 050		
PACKAGE	NLB 056			
JEDEC	N/A			
DxE	9.20 mm x 8.00 mm PACKAGE			
SYMBOL	MIN	NOM	MAX	NOTE
Α			1.20	PROFILE
A1	0.20			BALL HEIGHT
A2	0.85		0.97	BODY THICKNESS
D	9.20 BSC.			BODY SIZE
Е		8.00 BSC.		BODY SIZE
D1	4.50 BSC.			MATRIX FOOTPRINT
E1	6.50 BSC.			MATRIX FOOTPRINT
MD	10			MATRIX SIZE D DIRECTION
ME	14			MATRIX SIZE E DIRECTION
n		56		BALL COUNT
Øb	0.25	0.30	0.35	BALL DIAMETER
eE	0.50 BSC.			BALL PITCH
eD	0.50 BSC			BALL PITCH
SD / SE	0.25 BSC.			SOLDER BALL PLACEMENT
	A2 - A13,B1 - B14 C1,C2,C5,C6,C9,C10,C13,C14 D1,D2,D13,D14,E1,E2,E13,E14,F1,F2,F13,F14 G1,G2,G13,G14,H1,H2,H5,H6,H9,H10,H13,H14 J1 - J14, K2 - K13			DEPOPULATED SOLDER BALLS

### NOTES:

- DIMENSIONING AND TOLERANCING METHODS PER ASME Y14.5M-1994
- ALL DIMENSIONS ARE IN MILLIMETERS. 2
- BALL POSITION DESIGNATION PER JEP95, SECTION 4.3, SPP-010
- 4. e REPRESENTS THE SOLDER BALL GRID PITCH.
- SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION.

SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION.

 $\ensuremath{\mathsf{n}}$  IS THE NUMBER OF POPULTED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.

DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.

 $\stackrel{\textstyle \frown}{\bigtriangleup}$  SD AND SE ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW.

WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW SD OR SE = 0.000.

WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, SD OR SE = e/2

"+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED BALLS.

A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK, METALLIZED MARK INDENTATION OR OTHER MEANS.

10. OUTLINE AND DIMENSIONS PER CUSTOMER REQUIREMENT.

3507\ 16-038.22 \ 7.14.5



#### 4.3.2 NLA060—11.0 x 10.0 mm, 60-ball VFBGA

D1 D еD ○ 0.15 C (2X) SE /7 É E1 еĒ + 0 + HIGFEDCBA INDEX MARK В PIN A1 CORNER /9\ CORNER SD **TOP VIEW** ○ 0.15 C (2X) **BOTTOM VIEW** // 0.20 C A2 L<sub>A1</sub> ○ 0.08 C Ċ

## Figure 4.5 NLA060—60-ball VFBGA

PACKAGE	NLA 060			
JEDEC	N/A			
DxE	10.95 mm x 9.95 mm PACKAGE			
SYMBOL	MIN	NOM	MAX	NOTE
Α			1.20	PROFILE
A1	0.20			BALL HEIGHT
A2	0.85		0.97	BODY THICKNESS
D		10.95 BSC.		BODY SIZE
Е	9.95 BSC.			BODY SIZE
D1	6.50 BSC.			MATRIX FOOTPRINT
E1	8.50 BSC.			MATRIX FOOTPRINT
MD	14			MATRIX SIZE D DIRECTION
ME	18			MATRIX SIZE E DIRECTION
n	60			BALL COUNT
Øb	0.25	0.30	0.35	BALL DIAMETER
eЕ	0.50 BSC.			BALL PITCH
eD	0.50 BSC			BALL PITCH
SD / SE	0.25 BSC.			SOLDER BALL PLACEMENT
	A2-A17,B1-B18,C1,C2,C4-C15,C17,C18 D1-D18,E1,E2,E3,E4,E7,E8,E11,E12,E15,E16,E17,E18 F1,F2,F3,F4,F16,F17,F16,G1,G2,G3,Q4,G15,G16,G17,G18 H1,H2,H3,H4,H15,H16,H17,H18,J1,J2,J3,J4,J15,J16,J17,J18 K1,K2,K3,K4,K7,K6,K11,K12,K15,K16,K17,K18 L1-L18,M1,M2,M4-M15,M17,M18,M1-M18,P2-P17			DEPOPULATED SOLDER BALLS

SIDE VIEW

<u>/6\</u> 60X Ø b Ø 0.15 M C A B Ø 0.08 M C

- DIMENSIONING AND TOLERANCING METHODS PER ASME Y14.5M-1994.
- ALL DIMENSIONS ARE IN MILLIMETERS.
- BALL POSITION DESIGNATION PER JEP95, SECTION 4.3,
- e REPRESENTS THE SOLDER BALL GRID PITCH.
- SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION.
  - SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION.
  - $\ensuremath{\mathsf{n}}$  IS THE NUMBER OF POPULTED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.
- DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.
- SD AND SE ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW.
  - WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW SD OR SE = 0.000.
  - WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, SD OR SE = 0/2"+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED
- BALLS. A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK
- MARK, METALLIZED MARK INDENTATION OR OTHER MEANS. 10. OUTLINE AND DIMENSIONS PER CUSTOMER REQUIREMENT.



# 5. Revision History

Section	Description		
Revision A (January 3, 2006)			
	Initial Release under Publication Identification Number S71NS128NC0_01		
Revision A1 (March 1, 2006)			
Global	Changed the Publication Identification Number from S71NS128NC0_01 to S71NS-N_00		
Global	Added the MCP S71NS064NA0		
Revision A2 (June 13, 2006)			
Connection Diagrams	Corrected the grid reference for 56-ball connection diagram		
Revision A3 (October 10, 2006)			
Global	Added the S71NS064NA0-RT - the one using pSRAM Type 2		
Revision A4 (December 22, 2006)			
	Added S71NS064NA0-RA, S71NS064N80-RA		
Global	Deleted S71NS064NA0-RT		
	Added note to recommend S71NS128P and S71NS256P for new designs		
Revision A5 (March 2, 2007)			
Ordering Information	Revised Ordering Information and Valid Combinations for S71NS064N80		
Revision A6 (December 19, 2007)			
Global	Added ordering information and valid combinations for S71NS064NB0		
Revision A7 (March 26, 2008)			
Ordering Information	Added Low-Halogen package option for NS064N MCPs		
Ordering information	Added Note 2 for NS128N and NS256N MCPs		
Revision A8 (December 17, 2008)			
General Description	Updated Note 1 to refer to S71VS-R MCPs		
denotal bescription	Added 16 Mb Multiplexed pSRAM Type 3		
Ordering Information	Changed pSRAM Type 1 to Asynchronous		
	Changed pSRAM Type 1 to Asynchronous		
Valid Combinations	Changed S71NS064NB0BJWUN/S71NS064NB0BHWUN pSRAM to Type 3 with pSRAM speed 66 MHz		
Connection Diagrams	Changed typo in 56-ball pinout (K3 -> K1)		
Revision A9 (April 15, 2009)			
General Description	Added note regarding storage temperature		



### Colophon

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